12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20250730003.1
Qualification of RFAB using qualified Process Technology, Die Revision, Datasheet and BOM options for select devices
Change Notification / Sample Request

Date: July 30, 2025
To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments (TI). The details of this change are on the following pages, and are in alignment with our standard product change notification (PCN) process.

TI requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification, given that samples are not built ahead of the change.

The Proposed First Ship date in this PCN letter is the earliest possible date that customers could receive the changed material. It is our commitment that the changed device will not ship before that date. If samples are requested within the 60 day sample request window, customers will still have 30-days to complete their evaluation regardless of the proposed 1st ship date.

Changes outlined in this notification underscore our commitment to product longevity and supply continuity, as well as our continued efforts to transition to newer, more efficient manufacturing processes and technologies. Specifically, this particular notification is related to TI's multiyear transition plan for our two remaining 150-millimeter production lines (DFAB in Dallas, Texas, and SFAB in Sherman, Texas). SFAB closure activities are expected to begin by the end of 2025. DFAB will remain open with a smaller set of 200mm technologies and GaN.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the Change Management team. For sample requests or sample related questions, contact your local Field Sales Representative. As always, we thank you for your continued business.

TI values customer engagement and feedback related to TI changes. Customers should contact TI if there are questions or concerns regarding a change notification.

Change Management Team
SC Business Services

20250730003.1
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TPS79525DCQR	NULL
TPS79633DCQR	TPS79633DCQR
TPS79625DCQR	TPS79625DCQR
TPS79650DCQR	TPS79650DCQR
TPS79533DCQR	NULL
TPS79518DCQR	NULL

Technical details of this Product Change follow on the next page(s).

PCN Number:	20250730003	PCN Date:	July 30, 2025
Title:	Qualification of RFAB using qualified Process Technology, Die Revision, Datasheet and BOM options for select devices		
Customer Contact:	Change Management Team	Dept:	Quality Services
Proposed 1st Ship Date:	October 28, 2025	Sample requests accepted until:	September 28, 2025*

***Sample requests received after September 28, 2025 will not be supported.**

Change Type:

☐	Assembly Site	☒	Design	☐	Wafer Bump Material
☒	Assembly Process	☒	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☒	Wafer Fab Site
☐	Mechanical Specification	☐	Test Site	☒	Wafer Fab Material
☒	Packing/Shipping/Labeling	☐	Test Process	☒	Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the addition of RFAB using the LBC9 qualified process technology, and assembly BOM options for the devices listed below.

Group 1 and 2

Current Fab Site			Additional Fab Site		
Current Fab Site	**Process**	**Wafer Diameter**	**Additional Fab Site**	**Process**	**Wafer Diameter**
DL-LIN-2	LBC3	150 mm	RFAB	LBC9	300 mm

The die was also changed as a result of the process change.

Construction differences are as follows:

Group 1

Assembly/Test	TIEMA	TFME
Bond wire composition, diameter	Au, 1.5 mil	Cu, 1 mil
Lead Frame Finish	Matte Sn	NiPdAu
Mount Compound	8075531 and 4213245	SID#A-21
Mold Compound	8096890	SID#R-32
Wafer Thickness	267µm	780µm
Device Marking	Laser Dot	Molded Dimple

Group 2

Assembly/Test	HNA	TFME
Bond wire composition, diameter	Au, 1.5 mil	Cu, 1 mil
Mount Compound	SID#400728	SID#A-21
Mold Compound	SID#450179	SID#R-32
Wafer Thickness	267µm	780µm
Device Marking	Laser Dot	Molded Dimple

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below:

TEXAS INSTRUMENTS

TPS796

SLVS351Q – SEPTEMBER 2002 – REVISED JUNE 2025

Changes from Revision P (January 2015) to Revision Q (June 2025) **Page**

- Updated the numbering format for tables, figures, and cross-references throughout the document ... 1
- Changed device name to condensed *TPS796* to consolidate all voltage option devices under one device name ... 1
- Changed entire document to align with current family format ... 1
- Added new silicon (M3) devices to document ... 1
- Added nomenclature distinguishing between new chip and legacy chip information throughout document ... 1
- Changed *Features*, *Applications*, and *Description* sections ... 1
- Changed *Pin Configuration and Functions* section ... 3
- Added new silicon curves to *Typical Characteristics* section ... 8
- Added new chip block diagrams to *Functional Block Diagrams* section ... 14
- Added *Active Discharge (New Chip)* section ... 16
- Changed *Shutdown* section ... 16
- Changed *Undervoltage Lockout (UVLO)* section ... 16
- Changed *Regulator Protection* section and added subsections ... 17
- Added steady dropout state discussion in second paragraph to *Dropout Operation* section ... 19
- Added subsections to *Application Information* ... 20
- Changed *Design Parameters* table ... 25
- Changed *Detailed Design Procedure* section ... 25
- Changed *Application Curves* section ... 26
- Changed title from *Do's and Don'ts* to *Best Design Practices* ... 26
- Added *Estimating Junction Temperature* section ... 26
- Added M3 information to *Available Options* table ... 31

TEXAS INSTRUMENTS

TPS795

SLVS350K – OCTOBER 2002 – REVISED JUNE 2025

Changes from Revision J (May 2019) to Revision K (June 2025) **Page**

- Updated the numbering format for tables, figures, and cross-references throughout the document ... 1
- Added new silicon (M3) devices to document ... 1
- Added nomenclature distinguishing between new chip and legacy chip information throughout document ... 1
- Added portfolio device bullet to *Features* section ... 1
- Changed *Applications* section ... 1
- Changed *Description* section ... 1
- Changed *Pin Configuration and Functions* section ... 3
- Added new silicon curves to *Typical Characteristics* section ... 7
- Changed *Overview* section ... 14
- Added new chip diagrams to *Functional Block Diagrams* section ... 14
- Changed *Application Information* section ... 19
- Changed *Input and Output Capacitor Requirements* section ... 19
- Changed *Output Noise* section ... 20
- Changed *Application Curves* section ... 22
- Changed *Layout Examples* section ... 26
- Added *Device Nomenclature* section ... 29

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
TPS796	SLVS351P	**SLVS351P**	http://www.ti.com/product/TPS796
TPS795	SLVS350J	**SLVS350K**	http://www.ti.com/product/TPS795

Qual details are provided in the Qual Data Section.

Reason for Change:

These changes are part of our multiyear plan to transition products from our 200-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
RFAB	**RFB**	**USA**	**Richardson**

Die Rev:

Current	New
Die Rev [2P]	**Die Rev [2P]**
A	**A**

Assembly Site Information:

Assembly Site	Assembly Site Origin Code (20L)	Assembly Site Country Code (21L)	Assembly Site City
TIEMA	GNZ	MYS	MELAKA
HNA	HNT	THA	Ayutthaya
TFME	**NFM**	**CHN**	**Economic Development Zone**

Sample product shipping label (not actual product label):

Product Affected

Group 1

TPS79533DCQ	TPS79533DCQR	TPS79618DCQR	TPS79625DCQR
TPS79633DCQR			

Group 2

TPS79518DCQR	TPS79525DCQR	TPS79525DCQRG4	TPS79650DCQR

For alternate parts with similar or improved performance, please visit the product page on TI.com

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: TPS79633DCQRM3	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS79325DBVRM3	QBS Package Reference: TPS73701QDCQRM3Q1	QBS Package, Process Reference: TPS79633QDCQRM3Q1	QBS Package Reference: TPS73733DCQRM3
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	-	3/231/0	1/77/0	3/231/0
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	3/231/0	1/77/0	3/231/0
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	3/231/0	3/231/0	3/231/0
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	1/45/0	3/135/0
HTOL	B1	Life Test	125C	1000 Hours	-	3/231/0	-	-	-	-
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-	-	-	-
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes)	-	-	-	-	1/15/0	1/15/0	-
PD	C4	Physical Dimensions	Cpk>1.67	-	-	-	-	3/30/0	1/10/0	-
ESD	E2	ESD CDM	-	500 Volts	1/3/0	-	-	-	-	-
ESD	E2	ESD HBM	-	1000 Volts	-	-	1/3/0	-	-	-
LU	E4	Latch-Up	Per JESD78	-	-	-	1/3/0	-	-	-

Type	#	Test Name	Condition	Duration	Qual Device: TPS79633DCQRM3	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS79325DBVRM3	QBS Package Reference: TPS73701QDCQRM3Q1	QBS Package, Process Reference: TPS79633QDCQRM3Q1	QBS Package Reference: TPS73733DCQRM3
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	-	-	1/30/0	-	-	-
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	-	-	-	-

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device TPS79633DCQRM3 is qualified at MSL2 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-NPD-2406-118

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.